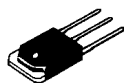


No.1398

2SC3483

NPN Triple Diffused Planar Type Silicon Transistor
FOR HIGH DEFINITION CRT DISPLAY HORIZONTAL
DEFLECTION OUTPUT APPLICATIONS

Features:

- High breakdown voltage and high reliability
- High switching speed: $t_f=0.3\mu s$ max.
- Capable of being mounted easily due to one-point fixing type plastic mold package

Absolute Maximum Ratings at $T_a=25^\circ C$

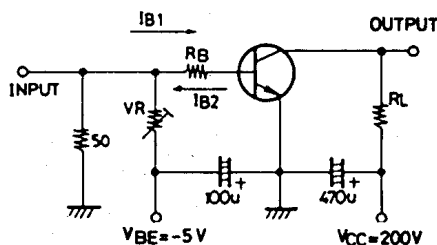
			unit
Collector to Base Voltage	V_{CB0}	1500	V
Collector to Emitter Voltage	V_{CE0}	800	V
Emitter to Base Voltage	V_{EB0}	7	V
Collector Current	I_C	2.5	A
Peak Collector Current	i_{cp}	10	A
Collector Dissipation	P_C $T_c=25^\circ C$	80	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

		min	typ	max	unit
Collector Cutoff Current	I_{CBO} $V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO} $V_{EB}=5V, I_C=0$			1	mA
DC Current Gain	h_{FE} $V_{CE}=5V, I_C=0.5A$	8			
Gain Bandwidth Product	f_T $V_{CE}=10V, I_C=0.5A$		3		MHz
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C=2A, I_B=0.6A$			8	V
B-E Saturation Voltage	$V_{BE(sat)}$ $I_C=2A, I_B=0.6A$			1.5	V
C-B Breakdown Voltage	$V(BR)_{CBO}$ $I_C=5mA, I_E=0$	1500			V
C-E Breakdown Voltage	$V(BR)_{CEO}$ $I_C=5mA, R_{BE}=\infty$	800			V
E-B Breakdown Voltage	$V(BR)_{EBO}$ $I_E=5mA, I_C=0$	7			V
Storage Time	t_{stg} $I_C=2A, I_{B1}=0.6A$			3.0	μs
Fall Time	t_f $I_{B2}=-1.2A, R_L=100\Omega$			0.3	μs

Switching Time Test Circuit

$PW=20\mu s$, Duty $\leq 1\%$



Case Outline 2022 (unit:mm)

